

Prompt and favorable examination on the merit is respectfully requested.

Respectfully submitted,



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Attachments:

Substitute Abstract
Appendix
Substitute Specification
Marked-up copy of specification

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APPENDIX

Changes to Abstract:

The following is a marked-up version of the amended Abstract.

ABSTRACT

The present invention provides a method for forming a thin film using a CVD process in which a large-scale vacuum exhaust unit or neutralization unit is not required, and a patterning step after the formation of the film is not required.

— A pattern 30a composed of ~~formed~~ of a monolayer is formed using (heptadecafluoro-1,1,2,2-tetrahydro)decyl-triethoxysilane on a surface 71 ~~for to forming~~ a thin film of a second glass substrate 7. Droplets 5 ~~composed of~~ formed of trimethylaluminum are placed on a plurality of parts of an upper surface 81 of a first substrate 8. The droplets 5 are placed at the positions corresponding to openings 31 of the monolayer pattern 30a. Both substrates 7 and 8 are placed in parallel with a predetermined distance therebetween, and the openings 31 and the droplets 5 are aligned with each other. While supplying nitrogen gas between the substrates 7 and 8, the second substrate 7 is heated to 300°C and retained for 5 minutes. Thereby, the droplets 5 are vaporized and the gas is fed into the openings 31. Aluminum resulting from decomposition by heat is deposited in these parts and aluminum thin films 50 are formed.

Changes to Specification:

A Substitute Specification is attached in accordance with 37 C.F.R. 1.125(b)(2).

Changes to Claims:

The following are marked-up versions of the amended claims:

~~(1)~~ 1. (Amended) A method for forming a thin film by chemical vapor deposition, comprising the steps of:

_____ placing a liquid containing a raw material for the thin film ~~on over one of a~~
part ~~or and~~ a plurality of parts of a substrate; and

_____ vaporizing the raw material for the thin film from the liquid so as to be fed to
~~one of a part or and~~ a plurality of parts of a surface ~~for to forming~~ the thin film ~~so as~~ to form
the thin film with a predetermined pattern ~~on over~~ the surface ~~for to forming~~ the thin film.

-(2) 2. (Amended) A-~~The~~ method for forming a thin film according to Claim 1,
~~wherein further including using~~ a surface of the substrate ~~is used as a surface for to placing~~
the liquid, and ~~forming~~ the thin film ~~is formed~~ in a region other than the region in which the
liquid is placed on the surface ~~for to placing~~ the liquid.

-(3) 3. (Amended) A-~~The~~ method for forming a thin film according to Claim 1,
~~wherein further including placing~~ a first substrate ~~for to placing~~ the liquid and a second
substrate ~~for to forming form~~ the thin film ~~are placed so that the surface for to placing~~ the
liquid of the first substrate faces the surface ~~for to forming~~ the thin film of the second
substrate, and ~~vaporizing~~ the raw material for the thin film ~~is vaporized~~ from the liquid placed
on ~~one of a part or and~~ a plurality of parts of the first substrate so as to be fed to the surface
~~for to forming~~ the thin film of the second substrate.

-(4) 4. (Amended) A-~~The~~ method for forming a thin film according to Claim 3,
~~wherein further including heating~~ the surface ~~for to forming~~ the thin film of the second
substrate ~~is heated~~ to a temperature at which a vaporized substance of the raw material for the
thin film is decomposable, and ~~heating~~ the first substrate ~~is heated~~ to a temperature at which
the raw material for the thin film is vaporized from the liquid by the heat radiated from the
second substrate.

5. (Twice Amended) A-~~The~~ method for forming a thin film according to
Claim 1, further ~~comprising including~~, before the step of placing the liquid, ~~the step of~~

forming an active region and an inactive region for the chemical vapor deposition in the surface ~~for to forming~~ the thin film so that the thin film is selectively deposited.

~~(6)~~ 6. (Amended) ~~A-~~The method for forming a thin film according to Claim 5, ~~wherein further including performing~~ the formation of the active region and the inactive region for the chemical vapor deposition ~~is performed~~ by forming a self-assembled film on the surface ~~for to forming~~ the thin film having hydroxyl groups using a silane derivative represented by ~~the a~~ general formula RSiX_3 (wherein R is a fluoroalkyl group in which terminal hydrogen of the alkyl group is replaced with fluorine, and X is an alkoxy group or halogen group); and performing ultraviolet irradiation on the self-assembled film through a photomask or performing electron beam irradiation on necessary parts of the self-assembled film so that the self-assembled film in a region ~~for to forming~~ the active region for the chemical vapor deposition is removed.

7. (Twice Amended) ~~A-~~The method for forming a thin film according to Claim 1, ~~wherein further including performing~~ the step of vaporizing the raw material for the thin film ~~is performed~~ while supplying inert gas, hydrogen gas, or a mixture of inert gas and hydrogen gas parallel to the surface ~~for to placing~~ the liquid of the substrate.

8. (Twice Amended) ~~A-~~The method for forming a thin film according to Claim 1, ~~wherein further including performing~~ the step of placing the liquid ~~is performed~~ by an ink-jet method.

~~(9)~~ 9. (Amended) An electronic apparatus, comprising:
~~a~~ the thin film formed by the ~~above~~ method according to claim 1, the thin film being used as an electrode.